Approval Sheet

Customer	
Product Number	**M2UK-2GMFQCH4-M**
Module speed	**PC2-4200**
Pin	**240 Pin**
CL-tRCD-tRP	**4-4-4**
Operating Temp	**0**°C **~ 85**°C
Date	**24th March 2020**

Rev 1.0

The Total Solution For Industrial Flash Storage

1. Features

Key Parameter

Industry Nomenclature	Data Rate MT/s			tRCD (ns)	tRP (ns)	tRC (ns)
	CL=3	CL=4	CL=5			
PC2-4200	400	533	-	15	15	60

- JEDEC Standard 240-pin Dual In-Line Memory Module
- Intend for 266MHz applications
- Inputs and Outputs are SSTL-18 compatible
- VDD=VDDQ= 1.8 Volt ± 0.1
- Differential clock input
- All inputs are sampled at the positive going edge of the system clock
- Bi-Directional data strobe with one clock cycle preamble and one-half clock post-amble
- Address and control signals are fully synchronous to positive clock edge.
- Auto Refresh (CBR) and Self Refresh Modes support.
- Serial Presence Detect with EEPROM
- Automatic and controlled precharge commands.
- 14/10/2 Addressing (row/column/rank)-2GB
- Auto & self refresh 7.8μs (Tc ≤ +85°C)
- Golden Contactor
- SDRAM Operation Temperature
  - 0°C ≤ Tc ≤ +85°C
- Programmable Device Operation:
  - Burst Type: Sequential or Interleave
  - Operation: Burst Read and Write
  - Device CAS# Latency: 3,4,5
  - Burst Length: 4, 8
- RoHS Compliant *(Section 12)*

2. Ordering Information

DDR2 UDIMM						
Part Number	Density	Speed	DIMM Organization	Number of DRAM	Number of rank	ECC
M2UK-2GMFQCH4-M	2GB	PC2-4200	256M x64	16	2	N/A

3. Pin Configurations (Front side/Back side)

–x64 UDIMM

Front								Back							
Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	VREF	31	DQ19	61	A4	91	VSS	121	VSS	151	VSS	181	VDDQ	211	DM5
2	VSS	32	VSS	62	VDDQ	92	/DQS5	122	DQ4	152	DQ28	182	A3	212	NC
3	DQ0	33	DQ24	63	A2	93	DQS5	123	DQ5	153	DQ29	183	A1	213	VSS
4	DQ1	34	DQ25	64	VDD	94	VSS	124	VSS	154	VSS	184	VDD	214	DQ46
5	VSS	35	VSS	65	VSS	95	DQ42	125	DM0	155	DM3	185	CK0	215	DQ47
6	/DQS0	36	/DQS3	66	VSS	96	DQ43	126	NC	156	NC	186	/CK0	216	VSS
7	DQS0	37	DQS3	67	VDD	97	VSS	127	VSS	157	VSS	187	VDD	217	DQ52
8	VSS	38	VSS	68	NC	98	DQ48	128	DQ6	158	DQ30	188	A0	218	DQ53
9	DQ2	39	DQ26	69	VDD	99	DQ49	129	DQ7	159	DQ31	189	VDD	219	VSS
10	DQ3	40	DQ27	70	A10	100	VSS	130	VSS	160	VSS	190	BA1	220	CK2
11	VSS	41	VSS	71	BA0	101	SA2	131	DQ12	161	NC	191	VDDQ	221	/CK2
12	DQ8	42	NC	72	VDDQ	102	NC	132	DQ13	162	NC	192	/RAS	222	VSS
13	DQ9	43	NC	73	/WE	103	VSS	133	VSS	163	VSS	193	/S0	223	DM6
14	VSS	44	VSS	74	/CAS	104	/DQS6	134	DM1	164	NC	194	VDDQ	224	NC
15	/DQS1	45	NC	75	VDD	105	DQS6	135	NC	165	NC	195	ODT0	225	VSS
16	DQS1	46	NC	76	NC	106	VSS	136	VSS	166	VSS	196	NC/A13	226	DQ54
17	VSS	47	VSS	77	NC	107	DQ50	137	CK1	167	NC	197	VDD	227	DQ55
18	NC	48	NC	78	VDDQ	108	DQ51	138	/CK1	168	NC	198	VSS	228	VSS
19	NC	49	NC	79	VSS	109	VSS	139	VSS	169	VSS	199	DQ36	229	DQ60
20	VSS	50	VSS	80	DQ32	110	DQ56	140	DQ14	170	VDDQ	200	DQ37	230	DQ61
21	DQ10	51	VDDQ	81	DQ33	111	DQ57	141	DQ15	171	NC	201	VSS	231	VSS
22	DQ11	52	CKE0	82	VSS	112	VSS	142	VSS	172	VDD	202	DM4	232	DM7
23	VSS	53	VDD	83	/DQS4	113	/DQS7	143	DQ20	173	NC	203	NC	233	NC
24	DQ16	54	NC/BA2	84	DQS4	114	DQS7	144	DQ21	174	NC/A14	204	VSS	234	VSS
25	DQ17	55	NC	85	VSS	115	VSS	145	VSS	175	VDDQ	205	DQ38	235	DQ62
26	VSS	56	VDDQ	86	DQ34	116	DQ58	146	DM2	176	A12	206	DQ39	236	DQ63
27	/DQS2	57	A11	87	DQ35	117	DQ59	147	NC	177	A9	207	VSS	237	VSS
28	DQS2	58	A7	88	VSS	118	VSS	148	VSS	178	VDD	208	DQ44	238	VDDSPD
29	VSS	59	VDD	89	DQ40	119	SDA	149	DQ22	179	A8	209	DQ45	239	SA0
30	DQ18	60	A5	90	DQ41	120	SCL	150	DQ23	180	A6	210	VSS	240	SA1

4. Architecture

Pin Definition

Pin Name	Description	Pin Name	Description
A0–A15	SDRAM address bus	CK0–CK2	SDRAM clocks (positive line of differential pair)
BA0–BA2	SDRAM bank select	/CK0–/CK2	SDRAM clocks (negative line of differential pair)
/RAS	SDRAM row address strobe	SCL	I^2C serial bus clock for EEPROM
/CAS	SDRAM column address strobe	SDA	I^2C serial bus data line for EEPROM
/WE	SDRAM write enable	SA0-SA2	I^2C slave address select for EEPROM
/S0-/S1	DIMM Rank Select Lines	VDD*	SDRAM core power supply
CKE0–CKE1	SDRAM clock enable lines	VDDQ*	SDRAM I/O Driver power supply
ODT0–ODT1	On-die termination control lines	VREF	SDRAM I/O reference supply
DQ0–DQ63	DIMM memory data bus	VSS	Power supply return (ground)
CB0–CB7	DIMM ECC check bits	VDDSPD	Serial EEPROM positive power supply
DQS0–DQS8	SDRAM data strobes (positive line of differential pair)	NC	Spare pins (no connect)
/DQS0–/DQS8	SDRAM data strobes (negative line of differential pair)	TEST	Used by memory bus analysis tools (unused on memory DIMMs)
DM0–DM8	SDRAM data masks/high data strobes (x8-based x72 DIMMs)	RESET	Not used on UDIMM
*The VDD and VDDQ pins are tied common to a single power-plane on these designs.			

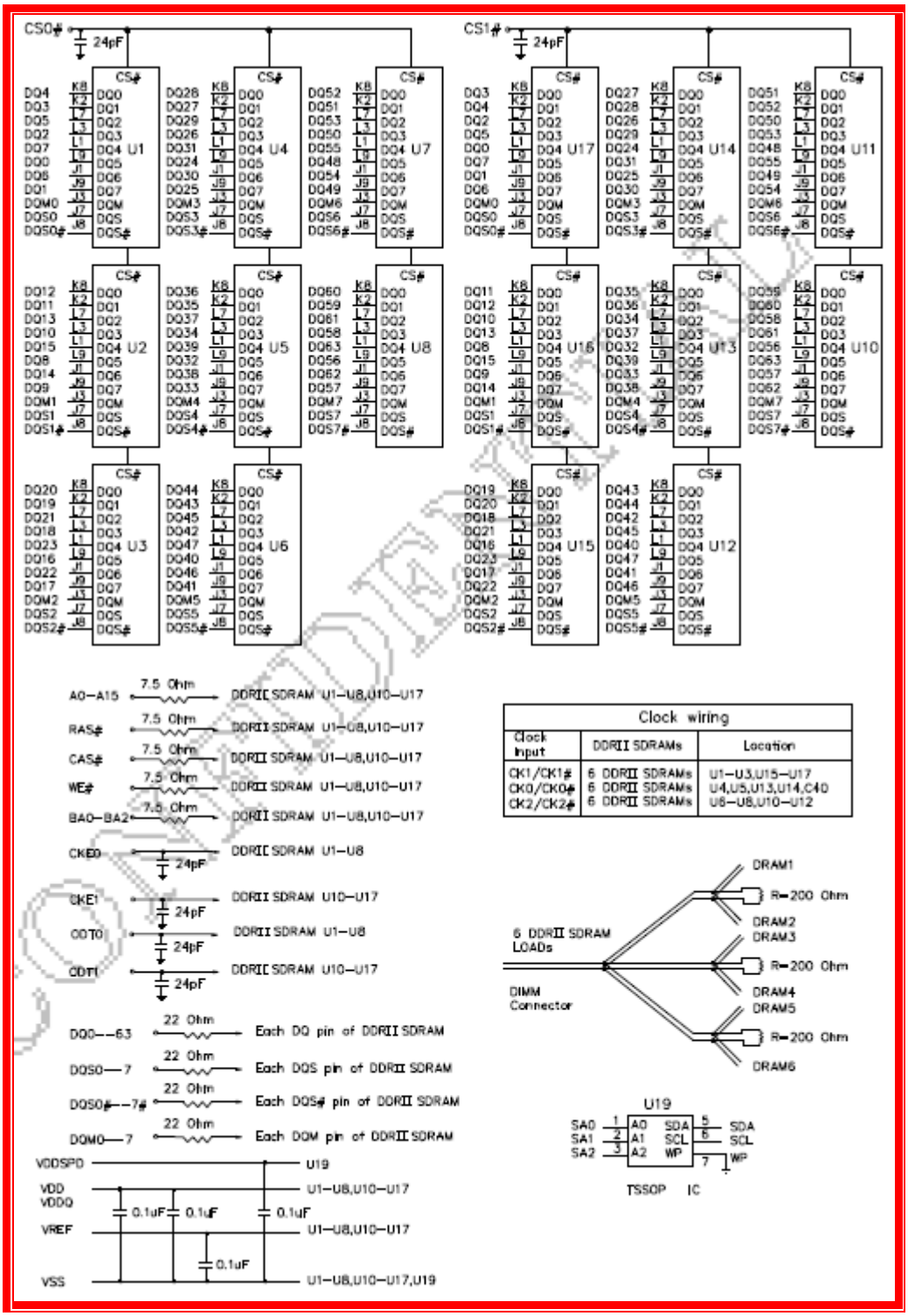
5. Input/Output Functional Description

Symbol	Type	Polarity	Function
CK0 - /CK0 CK1 - /CK1	Input	Cross point	The system clock inputs. All address and command lines are sampled on the cross point of the rising edge of CK and falling edge of /CK. A Delay Locked Loop (DLL) circuit is driven from the clock inputs and output timing for read operations is synchronized to the input clock.
CKE[1:0]	Input	Active High	Activates the DDR2 SDRAM CK signal when high and deactivates the CK signal when low. By deactivating the clocks, CKE low initiates the Power Down mode or the Self Refresh mode.
/S[1:0]	Input	Active Low	Enables the associated DDR2 SDRAM command decoder when low and disables the command decoder when high. When the command decoder is disabled, new commands are ignored but previous operations continue. Rank 0 is selected by /S0; Rank 1 is selected by /S1.
/RAS, /CAS, /WE	Input	Active Low	When sampled at the cross point of the rising edge of CK and falling edge of CK and CAS, RAS, and WE define the operation to be executed by the SDRAM.
BA[2:0]	Input	—	Selects which DDR2 SDRAM internal bank of four or eight is activated.
ODT[1:0]	Input	Active High	Asserts on-die termination for DQ, DM, DQS, and /DQS signals if enabled via the DDR2 SDRAM mode register.
A[9:0], A10/AP, A[15:11]	Input	—	During a Bank Activate command cycle, defines the row address when sampled at the cross point of the rising edge of CK and falling edge of /CK. During a Read or Write command cycle, defines the column address when sampled at the cross point of the rising edge of CK and falling edge of /CK. In addition to the column address, AP is used to invoke autoprecharge operation at the end of the burst read or write cycle. If AP is high, autoprecharge is selected and BA0-BAn defines the bank to be precharged. If AP is low, autoprecharge is disabled. During a Precharge command cycle, AP is used in conjunction with BA0-BAn to control which bank(s) to precharge. If AP is high, all banks will be precharged regardless of the state of BA0-BAn inputs. If AP is low, then BA0-BAn are used to define which bank to precharge.
DQ[63:0]	In/Out	—	Data Input/Output pins.
DM[7:0]	Input	Active High	The data write masks, associated with one data byte. In Write mode, DM operates as a byte mask by allowing input data to be written if it is low but blocks the write operation if it is high. In Read mode, DM lines have no effect.

DQS[7:0], /DQS[7:0]	In/Out	Cross point	The data strobes, associated with one data byte, sourced with data transfers. In Write mode, the data strobe is sourced by the controller and is centered in the data window. In Read mode, the data strobe is sourced by the DDR2 SDRAMs and is sent at the leading edge of the data window. /DQS signals are complements, and timing is relative to the crosspoint of respective DQS and /DQS. If the module is to be operated in single ended strobe mode, all /DQS signals must be tied on the system board to VSS and DDR2 SDRAM mode registers programmed appropriately.
VDD, VDDSPD, VSS	Supply	—	Power supplies for core, I/O, Serial Presence Detect, Thermal sensor, and ground for the module.
VREF	Supply	—	Reference voltage for SSTL18 inputs.
SDA	In/Out	—	This is a bidirectional pin used to transfer data into or out of the SPD EEPROM or Thermal sensor. A resistor must be connected from the SDA bus line to VDDSPD on the system planar to act as a pull up.
SCL	Input	—	This signal is used to clock data into and out of the SPD EEPROM and Thermal sensor.
SA[1:0]	Input	—	Address pins used to select the Serial Presence Detect base address.
TEST	In/Out	—	The TEST pin is reserved for bus analysis tools and is not connected on normal memory modules (SO-DIMMs).
/Event	Wire-OR Out	Active Low	The optional EVENT pin is reserved for use to flag critical module temperatures and is used in conjuction with a SPD temperture sensing option.

6. Function Block Diagram:

- (2 Ranks, 128Mx8 DDR2 base SDRAM UDIMM)



7. AC & DC Operating Conditions

7.1 Recommended DC operating Conditions

Symbol	Parameter	Rating			Units	NOTE
		Min.	Typ.	Max.		
V_{DD}	Supply Voltage	1.7	1.8	1.9	V	
V_{DDL}	Supply Voltage for DLL	1.7	1.8	1.9	V	4
V_{DDQ}	Supply Voltage for Output	1.7	1.8	1.9	V	4
V_{REF}	Input Reference Voltage	0.49*V_{DDQ}	0.50*V_{DDQ}	0.51*V_{DDQ}	mV	1,2
V_{TT}	Termination Voltage	V_{REF}-0.04	V_{REF}	V_{REF}+0.04	V	3

NOTE : There is no specific device V_{DD} supply voltage requirement for SSTL-1.8 compliance. However under all conditions V_{DDQ} must be less than or equal to VDD.

1. The value of V_{REF} may be selected by the user to provide optimum noise margin in the system. Typically the value of V_{REF} is expected to be about 0.5 x V_{DDQ} of the transmitting device and V_{REF} is expected to track variations in V_{DDQ}.
2. Peak to peak AC noise on V_{REF} may not exceed +/-2% V_{REF}(DC).
3. V_{TT} of transmitting device must track V_{REF} of receiving device.
4. AC parameters are measured with V_{DD}, V_{DDQ} and V_{DDL} tied together.

7.2 DRAM Operating Temperature Condition

Symbol	Parameter		Rating	Units	Note
T_{OPER}	Operating Temperature Range	Normal Temperature	0 to 85	°C	1,2

Note:

1. Operating Temperature TOPER is the case surface temperature on the center/top side of the DRAM.
2. T_{CASE} > 85°C ➔ T_{REFI} = 3.9μs. All DRAM specification only support 0°C < T_{CASE} < 85°C

7.3 Input DC / AC Logic Level

Symbol	Parameter	Min.	Max.	Units	Note
V_{IH}(DC)	DC input logic high	V_{REF}+0.125	V_{DDQ}+0.3	V	

V_{IL}(DC)	DC input logic low	-0.3	V_{REF}-0.125	V	
V_{IH}(AC)	AC input logic high	V_{REF}+0.200	-	V	1
V_{IL}(AC)	AC input logic low	-	V_{REF}-0.200	V	1

NOTE :

1. For information related to VPEAK value, Refer to overshoot/undershoot specification in device operation and timing datasheet; maximum peak amplitude allowed for overshoot and undershoot.

7.4 AC Input Test Conditions

Symbol	Condition	Value	Units	NOTE
V_{REF}	Input reference voltage	0.5*V_{DDQ}	V	1
V_{SWING}(MAX)	Input signal maximum peak to peak swing	1.0	V	1
SLEW	Input signal minimum slew rate	1.0	V/ns	2,3

NOTE:

1. Input waveform timing is referenced to the input signal crossing through the $V_{IH/IL}$(AC) level applied to the device under test.
2. The input signal minimum slew rate is to be maintained over the range from V_{REF} to V_{IH}(AC) min for rising edges and the range from V_{REF} to V_{IL}(AC) max for falling edges as shown in the below figure.
3. AC timings are referenced with input waveforms switching from V_{IL}(AC) to V_{IH}(AC) on the positive transitions and V_{IH}(AC) to V_{IL}(AC) on the negative transitions.

8. Operating, Standby, and Refresh Currents

- 2GB UDIMM (2Ranks, 128Mx8 DDR2 SDRAMs)

Symbol	Parameter/Condition	PC2-4200	Unit
I_{DD0}	Operating Current: one bank; active/precharge; tRC = tRC (MIN); tCK = tCK (MIN); DQ, DM, and DQS inputs changing twice per clock cycle; address and control inputs changing once per clock cycle	960	mA
I_{DD1}	Operating Current: one bank; active/read/precharge; Burst = 2; tRC = tRC (MIN); CL=2.5; tCK = tCK (MIN); IOUT = 0mA; address and control inputs changing once per clock cycle	1120	mA
I_{DD2P}	Precharge Power-Down Standby Current: all banks idle; power-down mode; CKE ≤ VIL (MAX); tCK = tCK (MIN)	160	mA
I_{DD2N}	Idle Standby Current: CS ≥ VIH (MIN); all banks idle; CKE ≥ VIH (MIN); tCK = tCK (MIN); address and control inputs changing once per clock cycle	384	mA
I_{DD2Q}	Precharge Quiet Standby Current: All banks idle; is HIGH; CKE is HIGH; $t_{CK} = t_{CK\ (MIN)}$; Other control and address inputs are stable, Data bus inputs are floating.	384	mA
I_{DD3PF}	Active Power-Down Current: All banks open; tCK = tCK (MIN), CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are floating. MRS A12 bit is set to **low** (Fast Power-down Exit).	448	mA
I_{DD3PS}	Active Power-Down Current: All banks open; tCK = tCK (MIN), CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are floating. MRS A12 bit is set to **high** (Slow Power-down Exit).	320	mA
I_{DD3N}	Active Standby Current: one bank; active/precharge; CS ≥ VIH (MIN); CKE ≥ VIH (MIN); tRC = tRAS (MAX); tCK = tCK (MIN); DQ, DM, and DQS inputs changing twice per clock cycle; address and control inputs changing once per clock cycle	480	mA
I_{DD4W}	Operating Current: one bank; Burst = 2; writes; continuous burst; address and control inputs changing once per clock cycle; DQ and DQS inputs changing twice per clock cycle; CL=2.5; tCK = tCK (MIN)	1840	mA
I_{DD4R}	Operating Current: one bank; Burst = 2; reads; continuous burst; address and control inputs changing once per clock cycle; DQ and DQS outputs changing twice per clock cycle; CL = 2.5; tCK = tCK (MIN); IOUT = 0mA	1760	mA
I_{DD5}	Auto-Refresh Current: tRC = tRFC (MIN)	2400	mA
I_{DD6}	Self-Refresh Current: CKE ≤ 0.2V	112	mA
I_{DD7}	Operating Current: four bank; four bank interleaving with BL = 4, address and control inputs randomly changing; 50% of data changing at every transfer; tRC = tRC (min); IOUT = 0mA.	2960	mA

9. AC Timing Specifications

Symbol	Parameter	PC2-4200		Unit
		Min.	Max.	
t_{AC}	DQ output access time from CK/CK#	-0.50	+0.50	ns
t_{DQSCK}	DQS output access time from CK/CK#	-0.45	+0.45	ns
t_{CH}	CK high-level width	0.45	0.55	t_{CK}
t_{CL}	CK low-level width	0.45	0.55	t_{CK}
t_{HP}	Minimum half clk period for any given cycle; defined by clk high (t_{CH}) or clk low (t_{CL}) time	$t_{CH/L}$ min	-	t_{CK}
t_{CK}	Clock Cycle Time	3.75	8	ns
t_{DS}	DQ and DM input setup time(differential data strobe)	100	-	ps
t_{DH}	DQ and DM input hold time(differential data strobe)	225	-	ps
t_{IPW}	Input pulse width	0.6	-	t_{CK}
t_{DIPW}	DQ and DM input pulse width (each input)	0.35	-	t_{CK}
t_{HZ}	Data-out high-impedance time from CK/XK	-	t_{ACmax}	ns
$t_{LZ(DQS)}$	DQS low-impedance time from CK/XK	t_{ACmin}	t_{ACmax}	ns
$t_{LZ(DQ)}$	DQ low-impedance time from CK/XK	2*t_{AC} min	t_{AC} max	ns
t_{DQSQ}	DQS-DQ skew (DQS & associated DQ signals)	-	0.3	ns
t_{QHS}	Data hold Skew Factor	-	0.4	ns
t_{QH}	Data output hold time from DQS	t_{HP} - t_{QHS}	-	ns
t_{DQSS}	Write command to 1st DQS latching transition	-0.25	+0.25	t_{CK}
$t_{DQSL,(H)}$	DQS input low (high) pulse width (write cycle)	0.35	-	t_{CK}
t_{DSS}	DQS falling edge to CK setup time (write cycle)	0.2	-	t_{CK}
t_{DSH}	DQS falling edge hold time from CK (write cycle)	0.2	-	t_{CK}
t_{MRD}	Mode register set command cycle time	2	-	t_{CK}
t_{WPST}	Write postamble	0.40	0.60	t_{CK}
t_{WPRE}	Write preamble	0.35	-	t_{CK}

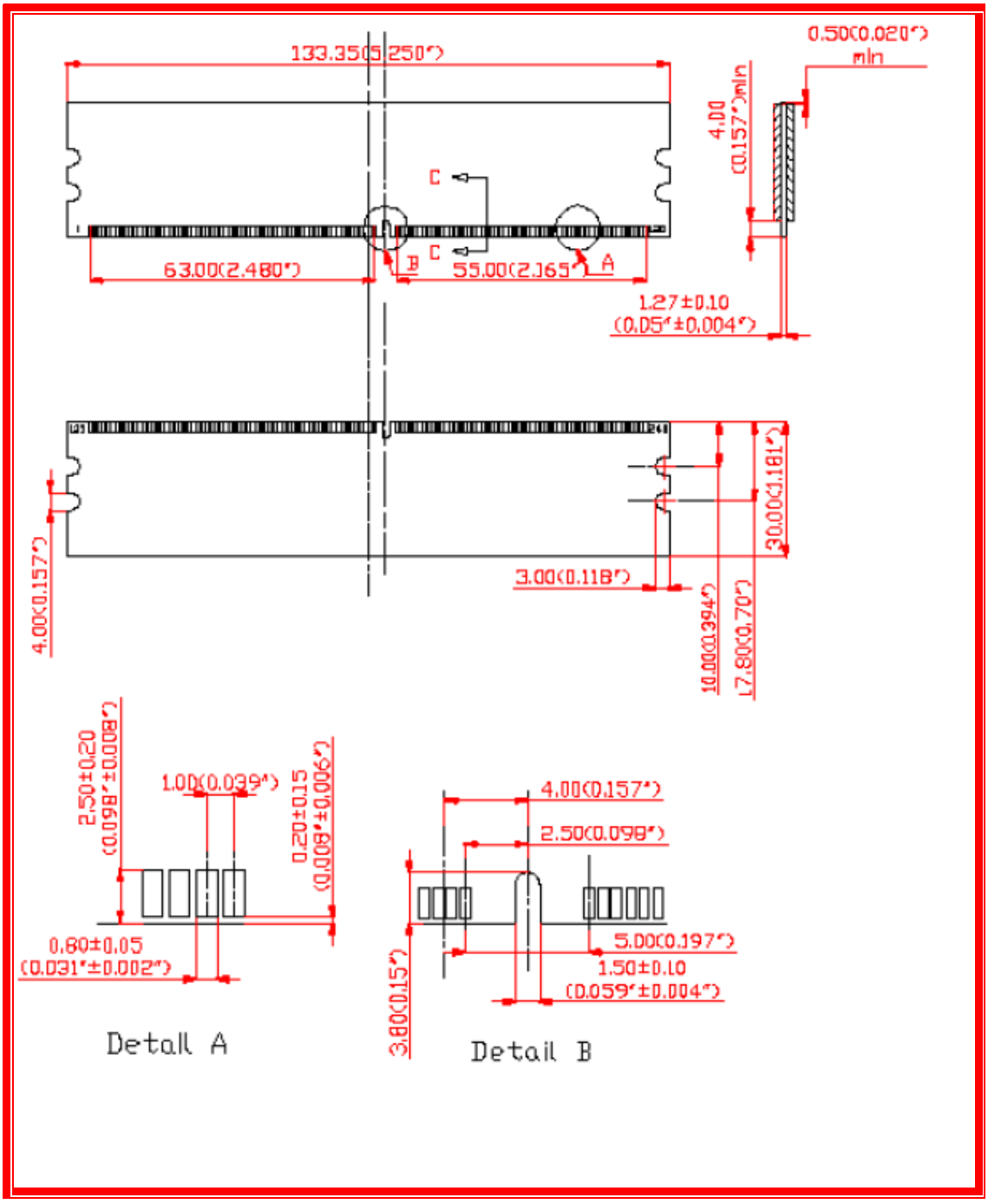
t_{IH}	Address and control input hold time	375	-	ps
t_{IS}	Address and control input setup time	250	-	ps
t_{RPRE}	Read preamble	0.90	1.10	t_{CK}
t_{RPST}	Read postamble	0.40	0.60	t_{CK}
t_{RRD}	Active bank A to Active bank B command	10	-	ns
t_{Delay}	Minimum time clocks remains ON after CKE asynchronously drops Low	$t_{IS} + t_{CK} + t_{IH}$	-	ns
t_{REFI}	Average Periodic Refresh Interval ($85^oC < T_{CASE} \leq 95^oC$)	3.9		µs
	Average Periodic Refresh Interval ($0^oC \leq T_{CASE} \leq 85^oC$)	7.8		µs
t_{OIT}	OCD drive mode output delay	0	12	ns
t_{CCD}	CAS# to CAS# delay	2		t_{CK}
t_{WR}	Write recovery time without Auto-Precharge	15	-	ns
t_{DAL}	Auto precharge write recovery + precharge time	WR+t_{RP}	-	t_{CK}
t_{WTR}	Internal write to read command delay	7.5	-	ns
t_{RTP}	Internal read to precharge command delay	7.5		ns
t_{XSNR}	Exit self refresh to a Non-read command	t_{RFC}+10		ns
t_{XSRD}	Exit self refresh to a Read command	200		t_{CK}
t_{XP}	Exit precharge power down to any Non- read command	2	-	t_{CK}
t_{XARD}	Exit active power down to read command	2	-	t_{CK}
t_{XARDS}	Exit active power down to read command	6-AL		t_{CK}
t_{CKE}	CKE minimum pulse width	3		t_{CK}
t_{AOND}	ODT turn-on delay	2	2	t_{CK}
t_{AON}	ODT turn-on	$t_{AC\ (min)}$	$t_{AC\ (max)}$ +1	ns
t_{AONPD}	ODT turn-on (Power down mode)	$t_{AC\ (min)}$ +2	2t_{CK} + $t_{AC(max)}$ +1	ns
t_{AOFD}	ODT turn-off delay	2.5	2.5	t_{CK}
t_{AOF}	ODT turn-off	$t_{AC(min)}$	$t_{AC(max)}$ +0.6	ns

t_{AOFPD}	ODT turn-off (Power down mode)	$t_{AC\ (min)}$+2	2.5t_{CK} + $t_{AC(max)}$ +1	ns
t_{ANPD}	ODT to power down entry latency	3		t_{CK}
t_{AXPD}	ODT power down exit latency	8		t_{CK}

10. Speed Grade Definition

Symbol	Parameter	PC2-4200		Unit
		Min	Max	
t_{RAS}	Row Active Time	45	70,000	ns
t_{RC}	Row Cycle Time	60	-	ns
t_{RCD}	RAS to CAS delay	15	-	ns
t_{RP}	Row Precharge Time	15	-	ns

11. Physical Dimension



Note: All dimensions are in millimeters (mils) and should be kept within a tolerance of ±0.15 (6), unless otherwise specified.

12. RoHS Declaration

innodisk

宜鼎國際股份有限公司
Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: http://www.innodisk.com/

RoHS 自我宣告書 (RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EM Flash and Dram products

一、 宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 及(EU) 2015/863 關於 RoHS 之規範要求。
Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) and (EU) 2015/863 requirement.

二、 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。
Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

三、 本公司聲明我們的產品符合 RoHS 指令的附件中(7a)、(7c-I)允許豁免。
We declare, our products permitted by the following exemptions specified in the Annex of the RoHS directive.
※ (7a) Lead in high melting temperature type solders(i.e. lead-based alloys containing 85% by weight or more lead).
※ (7C-I) Electrical and electronic components containing lead in a glass or ceramic other than dielectric ceramic in capacitors, e.g. piezoelectric devices, or in a glass or ceramic matrix compound.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
鉛 (Pb)	< 1000 ppm
汞 (Hg)	< 1000 ppm
鎘 (Cd)	< 100 ppm
六價鉻 (Cr 6+)	< 1000 ppm
多溴聯苯 (PBBs)	< 1000 ppm
多溴二苯醚 (PBDEs)	< 1000 ppm
鄰苯二甲酸二(2-乙基己基)酯 (DEHP)	< 1000 ppm
鄰苯二甲酸丁酯苯甲酯 (BBP)	< 1000 ppm
鄰苯二甲酸二丁酯 (DBP)	< 1000 ppm
鄰苯二甲酸二異丁酯 (DIBP)	< 1000 ppm

立 保 證 書 人 (Guarantor)

Company name 公司名稱： Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人： Randy Chien 簡川勝

Company Representative Title 公司代表人職稱： Chairman 董事長

Date 日期： 2018 / 07 / 01

Revision Log

Rev	Date	Modification
0.1	24th March 2020	Preliminary Edition
1.0	24th March 2020	Official Release